Hyperfast Rectifier, 2 A FRED Pt®

eSMP® Series



Top view Bottom view

SMF (DO-219AB)

Cathode ○—|◀|—○ Anode

FEATURES

- Hyperfast recovery time, reduced Q_{rr}, and soft recovery
- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Wave and reflow solderable
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

Pb e3 RoHS COMPLIANT HALOGEN FREE

DESIGN SUPPORT TOOLS

click logo to get started

3D Models Available

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber boost, lighting, piezo-injection, as high frequency rectifiers, and freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

PRIMARY CHARACTERISTICS	
$I_{F(AV)}$	2 A
V_R	200 V
V_F at I_F (typ. 125 °C)	0.75 V
t_{rr}	25 ns
T_J max.	175 °C
Package	SMF (DO-219AB)
Circuit configuration	Single

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage	V_{RRM}		200	V
Average rectified forward current	$I_{F(AV)}$	T_C = 150 °C (1)	2	A
Non-repetitive peak surge current	I_{FSM}	T_J = 25 °C	50	
Operating junction and storage temperature range	T_J, T_{Stg}		-65 to +175	°C

Note

(1) Device on PCB with 8 mm x 16 mm soldering lands

ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR}, V_R	I_R = 100 µA	200	-	-	V
Forward voltage	V_F	I_F = 2 A	-	0.88	0.95	
		I_F = 2 A, T_J = 125 °C	-	0.75	0.82	
Reverse leakage current	I_R	V_R = V_R rated	-	-	2	µA
		T_J = 125 °C, V_R = V_R rated	-	1	8	
Junction capacitance	C_T	V_R = 200 V	-	8	-	pF

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DYNAMIC RECOVERY CHARACTERISTICS (T_J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Reverse recovery time	t_{rr}	I_F = 1 A, dI_F/dt = 50 A/µs, V_R = 30 V		-	24	-	ns
		I_F = 0.5 A, I_R = 1 A, I_{rr} = 0.25 A		-	-	25	
		T_J = 25 °C	I_F = 2 A dI_F/dt = 200 A/µs V_R = 160 V	-	16	-	
		T_J = 125 °C		-	22	-	
Peak recovery current	I_{RRM}	T_J = 25 °C		-	2	-	A
		T_J = 125 °C		-	3	-	
Reverse recovery charge	Q_{rr}	T_J = 25 °C		-	16	-	nC
		T_J = 125 °C		-	30	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T_J, T_{Stg}		-65	-	175	°C
Thermal resistance, junction to case	R_{thJC}	Device mounted on PCB with 8 mm x 16 mm soldering lands	-	-	15	°C/W
Thermal resistance, junction to ambient	R_{thJA}	Device mounted on PCB with 2 mm x 3.5 mm soldering lands	-	-	130	°C/W
Approximate weight			0.015			g
			0.0005			oz.
Marking device		Case style SMF (DO-219AB)	MEH			

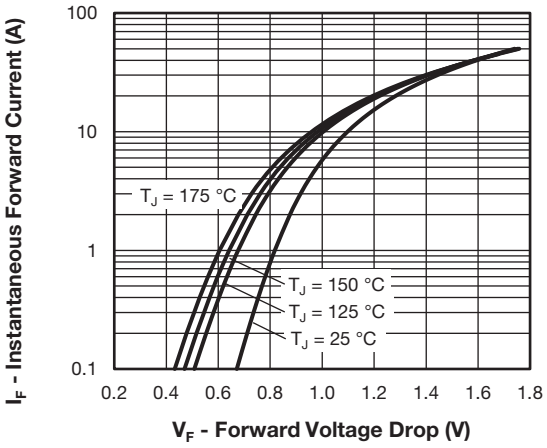


Fig. 1 - Typical Forward Voltage Drop Characteristics

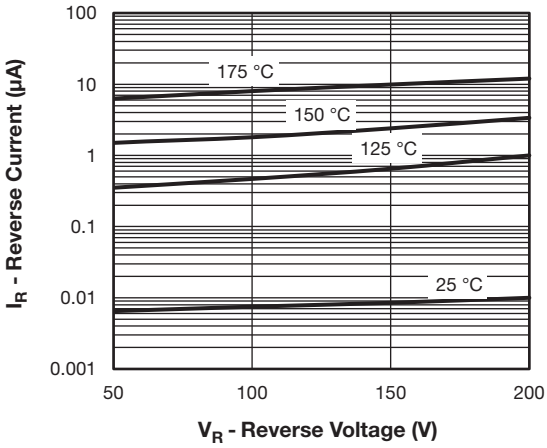


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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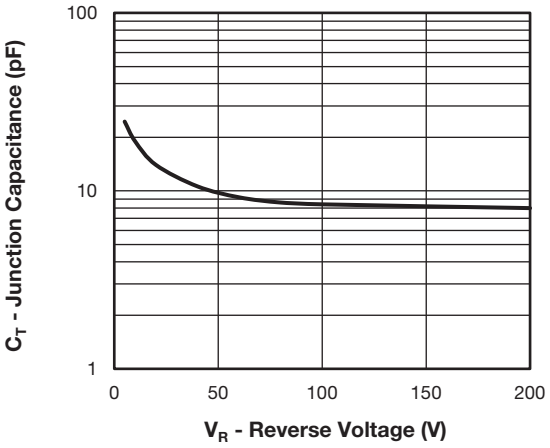


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

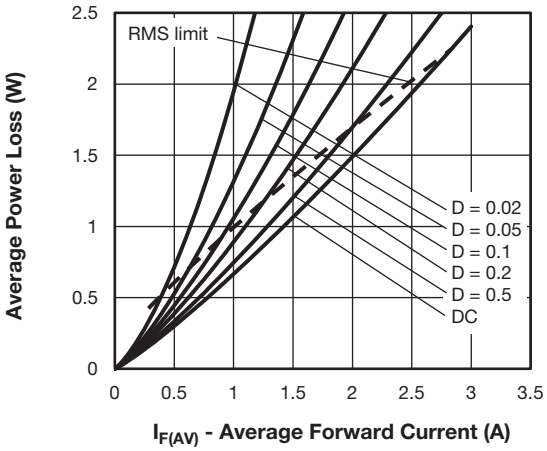


Fig. 5 - Forward Power Loss Characteristics

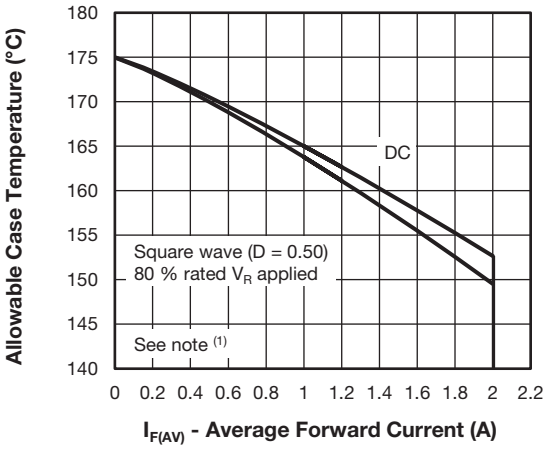


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

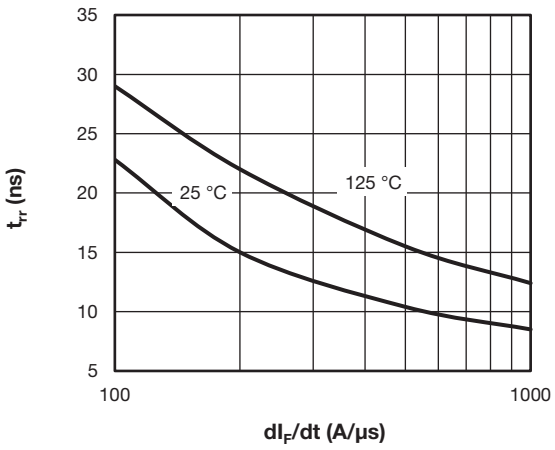


Fig. 6 - Typical Reverse Recovery Time vs. dI_F/dt

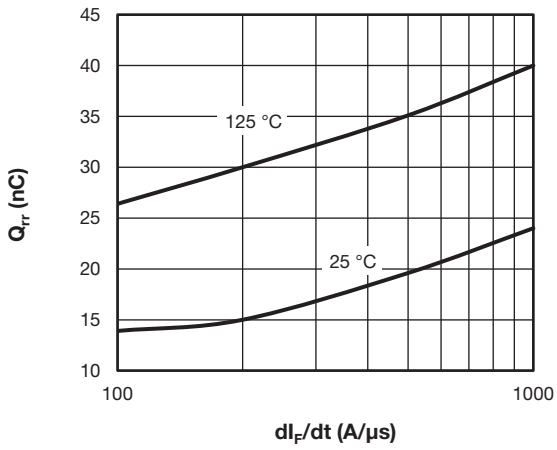
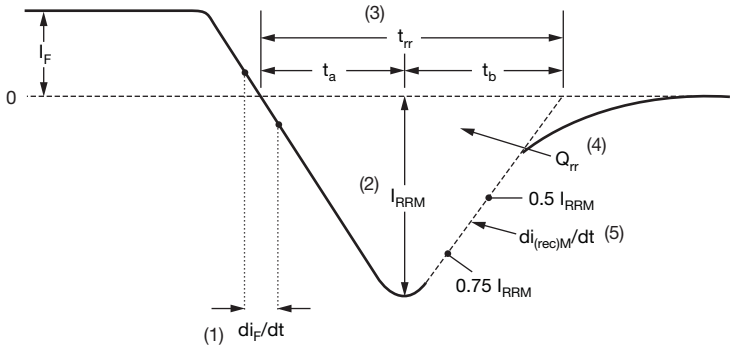


Fig. 7 - Typical Stored Charge vs. dI_F/dt

Note

(1) Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;
Pd = Forward power loss = $I_{F(AV)} \times V_{FM}$ at ($I_{F(AV)}$/D) (see fig. 5);
Pd_{REV} = Inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at V_{R1} = rated V_R

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(1) di_F/dt - rate of change of current through zero crossing

(2) I_{RRM} - peak reverse recovery current

(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

(4) Q_{rr} - area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 8 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code	VS-	2	E	F	H	02	H	M3
	1	2	3	4	5	6	7	8

1 - Vishay Semiconductors product

2 - Current rating (2 = 2 A)

3 - Circuit configuration:
E = single diode

4 - F = SMF package

5 - Process type,
H = hyperfast recovery

6 - Voltage code (02 = 200 V)

7 - H = AEC-Q101 qualified

8 - M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

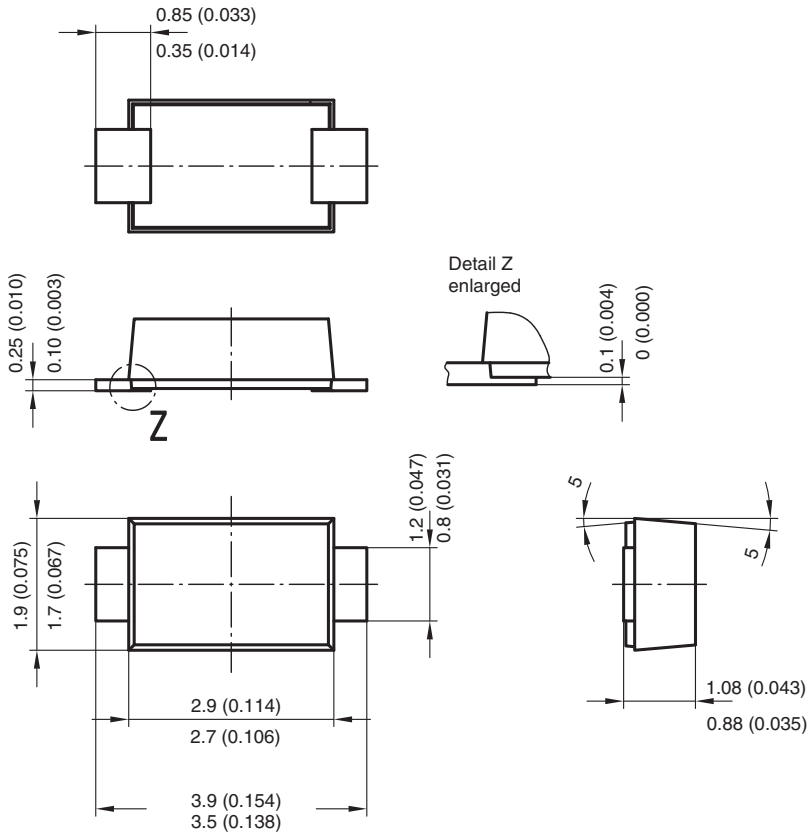
ORDERING INFORMATION (Example)			
PREFERRED P/N	**QUANTITY PER REEL**	**MINIMUM ORDER QUANTITY**	**PACKAGING DESCRIPTION**
VS-2EFH02HM3/I	10 000	10 000	13" diameter plastic tape and reel

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95572
Part marking information	www.vishay.com/doc?95618
Packaging information	www.vishay.com/doc?95577
SPICE model	www.vishay.com/doc?96013

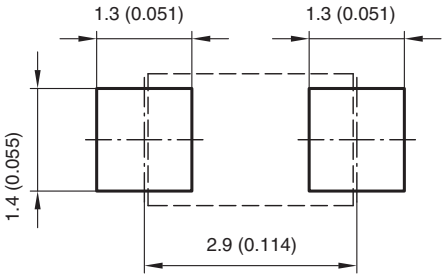
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SMF (DO-219AB)

DIMENSIONS in millimeters (inches)



Foot print recommendation:



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